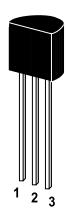
NPN Silicon Epitaxial Planar Transistor

TV VHF TUNER RF AMPLIFIER (FORWARD AGC)

The transistor is subdivided into three group, R . O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25℃)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	30	V
Collector Emitter Voltage	V _{CEO}	30	V
Emitter Base Voltage	V _{EBO}	4	V
Collector Current	I _C	20	mA
Collector Dissipation	P _{tot}	250	mW
Junction Temperature	T _j 150		$^{\circ}\!\mathbb{C}$
Storage Temperature Range	Ts	-55 to +150	$^{\circ}\!\mathbb{C}$







ST 2SC1393

Characteristics at T_{amb}=25℃

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V _{CE} =10V, I _C =2mA	R	h_{FE}	40	-	80	
	0	h_FE	60	-	140	-
	Υ	h_{FE}	90	-	180	
Collector Base Breakdown Voltage						
at I _C =10μA		$V_{(BR)CBO}$	30	-	-	V
Collector Emitter Breakdown Voltage						
at I _C =5mA		$V_{(BR)CEO}$	30	-	-	V
Emitter Base Breakdown Voltage						
at I _E =10μA		$V_{(BR)EBO}$	4	-	-	V
Collector Cutoff Current						
at V _{CB} =20V		I_{CBO}	-	-	0.1	μΑ
AGC Current						
I _E at G _{pe} =-30dB, f=200MHz		I_{AGC}	-	-10	-12	mA
Reverse Transfer Capacitance						
at V _{CB} =10V, f=1MHz		C_{re}	-	0.35	0.5	pF
Current Gain Bandwidth Product						
at V _{CE} =10V, I _C =3mA		f_T	400	700	-	MHz
Power Gain						
at V_{CE} =10V, f=200MHz, R_S =50 Ω , I_E =-3m	ıΑ	G_pe	20	24	-	dB
Noise Figure						
at V _{CE} =10V, I _E =-3mA						
f=200MHz, R _S =50Ω		NF	-	2.0	3.0	dB









SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)